

<b>PCN Number:</b>	20170613006		<b>PCN Date:</b>	June 21, 2017	
<b>Title:</b>	TPS65381QDAPRQ1 new die revision				
<b>Customer Contact:</b>	<a href="#">PCN Manager</a>		<b>Dept:</b>	Quality Services	
<b>Proposed 1<sup>st</sup> Ship Date:</b>	Dec. 21, 2017	<b>Estimated Sample Availability:</b>	Date provided at sample request		
<b>Change Type:</b>					
<input type="checkbox"/>	Assembly Site	<input checked="" type="checkbox"/>	Design	<input type="checkbox"/>	Wafer Bump Site
<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Data Sheet	<input type="checkbox"/>	Wafer Bump Material
<input type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change	<input type="checkbox"/>	Wafer Bump Process
<input type="checkbox"/>	Mechanical Specification	<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Wafer Fab Site
<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process	<input type="checkbox"/>	Wafer Fab Materials
				<input type="checkbox"/>	Wafer Fab Process
<b>PCN Details</b>					
<b>Description of Change:</b>					
Texas Instruments Incorporated is announcing the qualification of a new metal level only design revision to device TPS65381QDAPRQ1.					
The release of new design revision addresses the following fixes:					
- Timing violation to fix Scan (digital change only)					
- Vgs issue on two spare FETs (no impact on parametric, only to eliminate reliability concerns)					
<b>Reason for Change:</b>					
To correct known design issues to enable scan at production test and eliminate reliability concerns related to Vgs issue.					
<b>Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):</b>					
None					
<b>Changes to product identification resulting from this PCN:</b>					
None					
<b>Product Affected:</b>					
TPS65381QDAPRQ1					

**Automotive New Product Qualification Summary  
(As per AEC-Q100H and JEDEC Guidelines)**

**TPS65381AQDAPRQ1  
Approved March 20, 2017**

**Product Attributes**

<b>Attributes</b>	<b>Qual Device: TPS65381AQDAPRQ1</b>	<b>Product QBS Reference: TPS65381AQDAPRQ1</b>	<b>Product/Process/Package QBS Reference: TPS65300QPWPRQ1</b>
<b>Automotive Grade Level</b>	Grade 1	Grade 1	Grade 1
<b>Operating Temp Range</b>	-40°C to +125°C	-40°C to +125°C	-40°C to +125°C
<b>Product Function</b>	Power Management	Power Management	Power Management
<b>Wafer Fab Supplier</b>	DMOS5	DMOS5	DMOS5
<b>Die Revision</b>	C2	A0	A0
<b>Assembly Site</b>	Taiwan	Taiwan	Taiwan
<b>Package Designator</b>	DAP	DAP	PWP
<b>Ball/Lead Count</b>	32	32	24

- QBS: Qual By Similarity
- Qual device is stressed for MSL3

**Qualification Results**  
**Data Displayed as: Number of lots / Total sample size / Total failed**

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: TPS65381AQDA PRQ1	Product QBS Reference: TPS65381QD APRQ1	Product/Process/Package QBS Reference: TPS65300QPWPRQ1
<b>Test Group A – Accelerated Environment Stress Tests</b>									
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Automotive Preconditioning Level 3	260C peak	-	3/all/0	3/all/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 hours	-	3/231/0	3/231/0
	A3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 hours	-	3/231/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 cycles	-	3/227/0	3/227/0
			1	5	Bond Wire Pull	Post Temp Cycle 500 cycles	-	-	1/5/0
			1	5	Bond shear	Post Temp Cycle 500 cycles (for information only)	-	-	1/5/0
			3	12	SAM	Post Temp Cycle 500 cycles (for information only)	-	3/36/0	3/36/0
					Temperature Cycle, -65/150C	1000 cycles (for information only)	-	3/227/0	3/231/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle, -40/125C	1000 cycles	-	1/45/0	3/135/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 175C	500 hours	-	1/45/0	3/135/0
<b>Test Group B – Accelerated Lifetime Simulation Tests</b>									
HTOL	B1	JEDEC JESD22-A108	3	77	HTOL 125C	1000 hours	-	1/77/0 (rev. C1)	3/231/0
					HTOL	2000 hours	-	1/77/0	-

					125C	(for information only)		(rev. C1)	
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 hours	-	1/800/0 (rev. C1)	3/2400/0
<b>Test Group C – Package Assembly Integrity Tests</b>									
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Cpk>1.67	1/30/0	1/30/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Pull	Cpk>1.67	1/30/0	1/30/0	1/30/0
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability	-	-	1/15/0*	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	3/30/0*	3/30/0*
SBS	C5	AEC Q100-010	3	50	Solder Ball Shear (Cpk>1.67)	Post HTSL/Bump	NA	NA	NA
LI	C6	JEDEC JESD22-B105	1	50	Lead Integrity	-	NA	NA	NA
<b>Test Group D – Die Fabrication Reliability Tests</b>									
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDD	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
<b>Test Group E – Electrical Verification Tests</b>									
HBM	E2	AEC Q100-002	1	3	ESD - HBM - Q100	2000 V	1/3/0	1/3/0	1/3/0
CDM	E3	AEC Q100-011	1	3	ESD - CDM - Q100	500 V (all pins) 750 V (corner)	1/3/0	1/3/0	1/3/0

						pins)			
LU	E4	AEC Q100-004	1	6	Latch-up	RT and 125C	1/6/0	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Auto Electrical Distributi ons	Cpk>1.67 Room, hot, and cold test	1/30/0	3/90/0	3/90/0

**A1 (PC): Preconditioning:** Performed for THB, Biased HAST, AC, uHAST, & TC samples, as applicable.

**Operating Temperature by Automotive Grade Level:**

Grade 0 (or E): -40°C to +150°C  
Grade 1 (or Q): -40°C to +125°C  
Grade 2 (or T): -40°C to +105°C  
Grade 3 (or I): -40°C to +85°C

**E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):**

Room/Hot/Cold: HTOL, ED  
Room/Hot: THB/HAST, TC / PTC, HTSL, ELFR, ESD & LU  
Room: AC/uHAST

**Green/Pb-free Status:**

Qualified Pb-Free (SMT) and Green

Note: DSB data for solderability (NIRdAu) and Physical Dimensions (DAP) are taken using different devices with same package material and process by same assembly site.

**Quality and Reliability Data Disclaimer**

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Reliability data shows characteristic failure mechanisms of the specific environmental stress as documented in the industry standards for each stress condition.

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

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